



# CEP1012/CEB1012

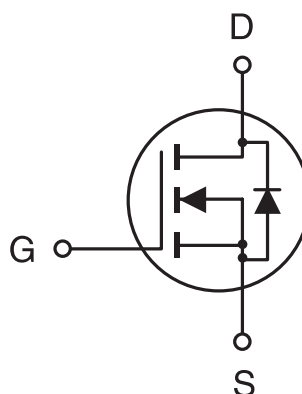
March 1998

## N-Channel Enhancement Mode Field Transistor

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### FEATURES

- 120V , 10A ,  $R_{DS(ON)}=120m\Omega$  @  $V_{GS}=10V$
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- TO-220 & TO-263 package.



### ABSOLUTE MAXIMUM RATINGS ( $T_c=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	120	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous -Pulsed	$I_D$	10	A
	$I_{DM}$	40	A
Drain-Source Diode Forward Current	$I_S$	10	A
Maximum Power Dissipation @ $T_c=25^{\circ}C$ Derate above $25^{\circ}C$	$P_D$	100	W
		0.8	W/ $^{\circ}C$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 to 150	$^{\circ}C$

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}C/W$

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## ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	120			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =120V, V <sub>GS</sub> =0V			25	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS <sup>a</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	2.8	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =10A		90	120	mΩ
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V	10			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A		6		S
DYNAMIC CHARACTERISTICS <sup>b</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> = 0V f =1.0MHz		602	800	pF
Output Capacitance	C <sub>OSS</sub>			155	210	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			67	100	pF
SWITCHING CHARACTERISTICS <sup>b</sup>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> =15A, V <sub>GS</sub> = 5V, R <sub>GEN</sub> = 51Ω		42	60	ns
Rise Time	t <sub>r</sub>			84	120	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			56	80	ns
Fall Time	t <sub>f</sub>			35	50	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =96V, I <sub>D</sub> = 10A, V <sub>GS</sub> =10V		29	60	nC
Gate-Source Charge	Q <sub>gs</sub>			4		nC
Gate-Drain Charge	Q <sub>gd</sub>			15		nC

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Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS <sup>a</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{V}, I_S = 10\text{A}$		0.86	1.2	V

### Notes

a. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

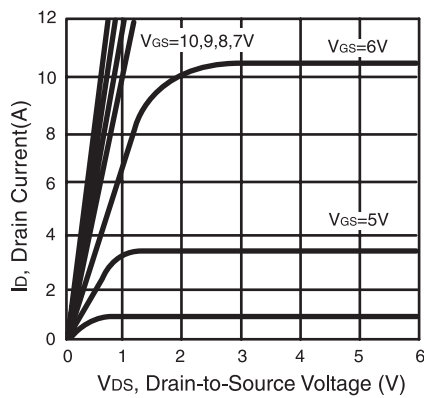


Figure 1. Output Characteristics

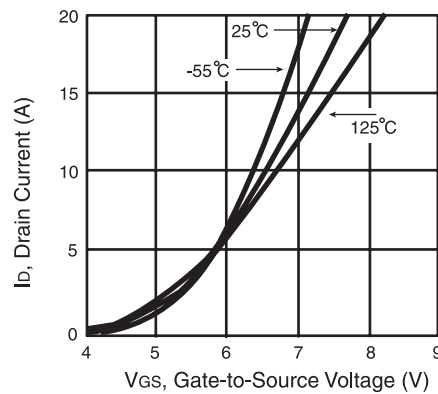


Figure 2. Transfer Characteristics

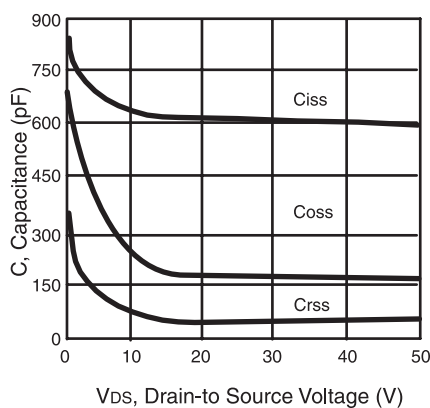


Figure 3. Capacitance

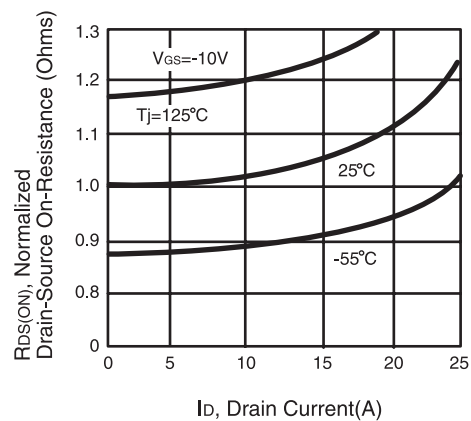
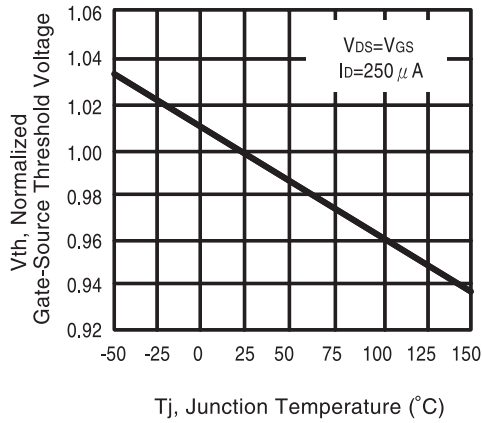


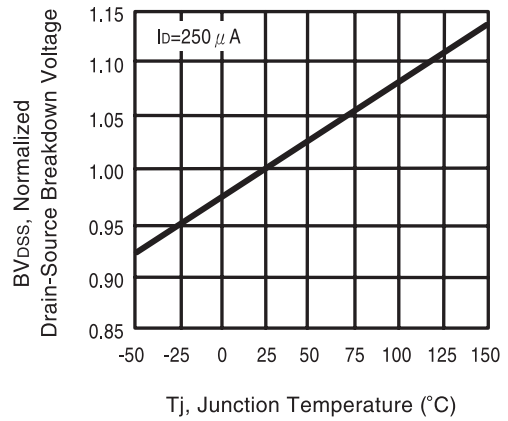
Figure 4. On-Resistance Variation with Drain Current and Temperature

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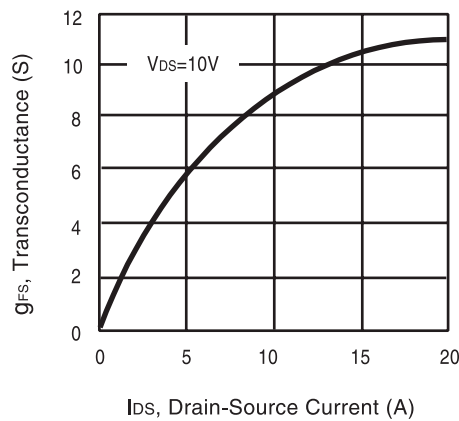
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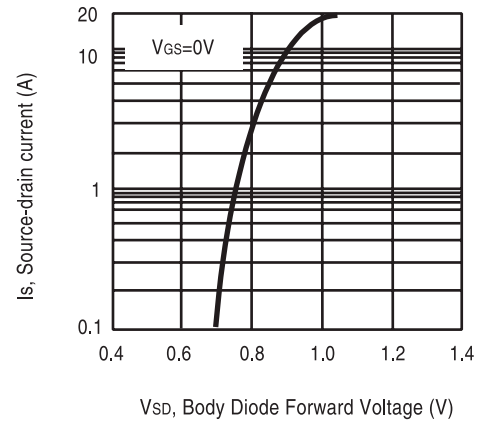
**Figure 5. Gate Threshold Variation with Temperature**



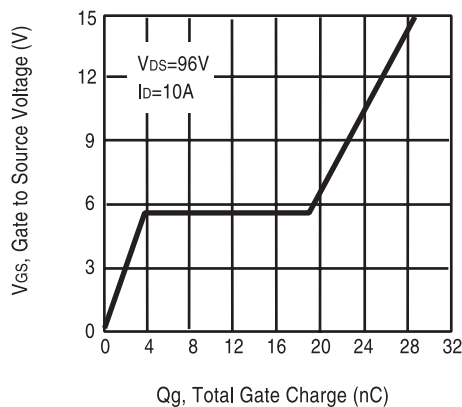
**Figure 6. Breakdown Voltage Variation with Temperature**



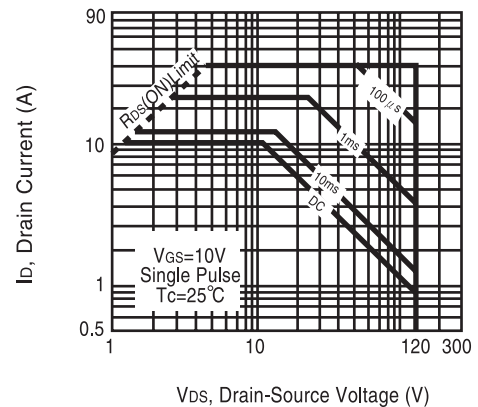
**Figure 7. Transconductance Variation with Drain Current**



**Figure 8. Body Diode Forward Voltage Variation with Source Current**



**Figure 9. Gate Charge**



**Figure 10. Maximum Safe Operating Area**

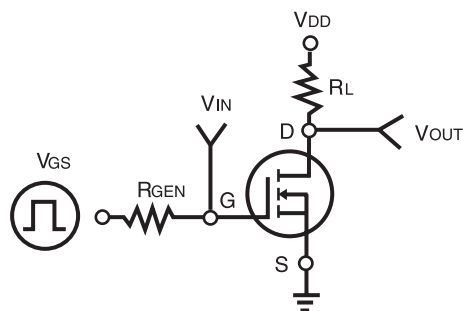


Figure 11. Switching Test Circuit

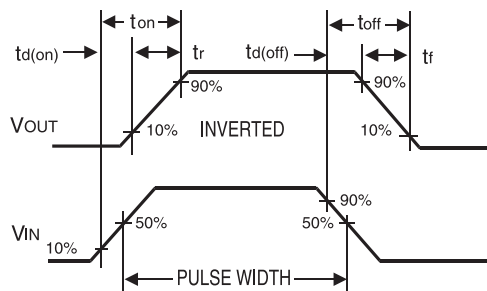


Figure 12. Switching Waveforms

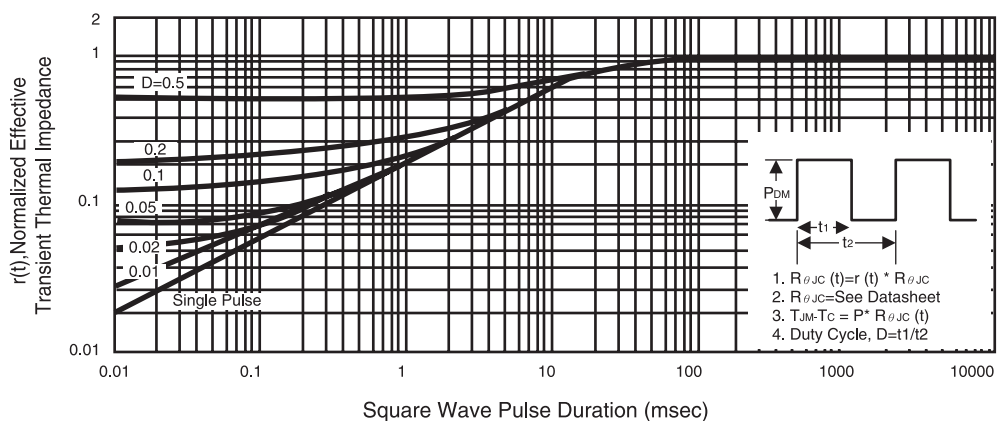


Figure 13. Normalized Thermal Transient Impedance Curve